ABSTRACT

A semiconductor device includes an active region that extends in a first direction and has a first width in a second direction that intersects the first direction, a first gate structure disposed on the active region, having a second width in the first direction and extending in the second direction, a first metal contact spaced apart from the first gate structure in the first direction, a first trench formed in the active region, and an insulating material that fills the first trench and forms a first active cut, wherein the first active cut defines a first metal region in the active region in which the first metal contact is located, and the first metal contact is placed off-center inside the first metal region and a length of a region where the first gate structure and the active region overlap is longer than that of the first and second trenches.

FIG. 2